L Number	Hits	Search Text	I DB	Time stamp
- 110000ET	32262		USPAT;	2004/08/26 10:54
	32202	double of dual of marcify, hears gate	US-PGPUB;	2004/00/20 10.54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	131356	fin	USPĀT;	2004/08/26 10:55
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1076015	, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	0004/00/05 74 05
-	1076015		USPAT;	2004/08/26 11:06
		under adj2 cut\$5 or recess\$5	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	244514	mosfet or misfet or fet or (mos or mis)	USPAT;	2004/08/25 17:05
		adj2 (transistor or device)	US-PGPUB;	
		,,,,,,,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	388909	(USPĀT;	2004/08/25 17:07
		adj2 (transistor or device)) or pmos or	US-PGPUB;	
		pmosfet or nmos or nmosfet or field adj5	EPO; JPO;	
		(transistor or device) or igfet or ig adj	DERWENT;	
	163236	fet	IBM_TDB USPAT;	2004/08/25 17:19
_	163236	((double or dual or multi\$4) near5 gate)	US-PGPUB;	2004/08/25 17:19
			EPO; JPO;	
ļ			DERWENT;	
			IBM TDB	
	352642	spacer	USPAT;	2004/08/26 11:05
			US-PGPUB;	
[EPO; JPO;	
:			DERWENT;	
	0000010		IBM_TDB	0004/00/06 11 16
-	2988210	insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin"	USPAT;	2004/08/26 11:16
1		or "si.sub.3 n.sub.4" or "si.sub3n.sub.4"	US-PGPUB; EPO; JPO;	
		01 51.5db.5 11.5db.4 01 51.5db511.5db.4	DERWENT;	
1			IBM TDB	
-	1834033	fill\$4 or refill\$4	USPAT;	2004/08/26 11:17
:			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/55 55 55
~	2823565	spacer or sidewall or wall or side adj2	USPAT;	2004/08/25 17:25
		wall	US-PGPUB;	
		İ '	EPO; JPO; DERWENT;	
			IBM TDB	
_	194700	(insulat\$4 or dielectric or oxide or	USPAT;	2004/08/25 17:26
		dioxide or nitride or "sio.sub.2" or "sin"	US-PGPUB;	
		or "si.sub.3 n.sub.4" or "si.sub3n.sub.4")	EPO; JPO;	
		with (fill\$4 or refill\$4)	DERWENT;	
			IBM_TDB	
-	12336	''	USPAT;	2004/08/25 17:27
		overhung or undercut\$5 or under adj2 cut\$5	US-PGPUB;	
		or recess\$5) same (insulat\$4 or dielectric	EPO; JPO;	•
		or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4"	DERWENT; IBM TDB	
		or "si.sub3n.sub.4")	TBM_IDB	
_	608	((fill\$4 or refill\$4) same (overhang\$4 or	USPAT;	2004/08/25 17:28
		overhung or undercut\$5 or under adj2 cut\$5	US-PGPUB;	
		or recess\$5) same (insulat\$4 or dielectric	EPO; JPO;	
		or oxide or dioxide or nitride or	DERWENT;	
		"sio.sub.2" or "sin" or "si.sub.3 n.sub.4"	IBM_TDB	
		or "si.sub3n.sub.4")) and (((double or		
		dual or multi\$4) near5 gate) or fin)	L	

	508	(((fill\$4 or refill\$4) same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4")) and (((double or dual or multi\$4) near5 gate) or fin)) and (spacer or sidewall or wall or side adj2 wall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:29
_	258	((((fill\$4 or refill\$4) same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4")) and (((double or dual or multi\$4) near5 gate) or fin)) and (spacer or sidewall or wall or side adj2 wall)) and ((mosfet or misfet or fet or (mos or mis) adj2 (transistor or device)) or pmos or pmosfet or nmos or nmosfet or field adj5 (transistor or device) or igfet or ig adj fet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:29
-	131548	fin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 10:55
_	33552	((double or dual or multi\$4) near5 gate\$2) or multigate\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 10:55
_	122	fin same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 11:03
_	131584	fin or finfet or finmos\$4 or finmis\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 11:04
_	137	<pre>(fin or finfet or finmos\$4 or finmis\$4) same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)</pre>	USPĀT; US-PGPUB; EPO; JPO; DERWENT;	2004/08/26 11:04
-	353136	spacer	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 11:06
	1077720	overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 11:06
-	353136	spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 11:06
_	102	<pre>((fin or finfet or finmos\$4 or finmis\$4) same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)) and ((overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) or spacer)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:07
-	2992433	insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 11:17

	1006500		1	10004/00/06 11 10
-	1836583	fill\$4 or refill\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 11:18
_	12374	(fill\$4 or refill\$4) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4") same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:19
	306	((fill\$4 or refill\$4) same (insulat\$4 or dielectric or oxide or dielectric or oxide or dielectric or oxide or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4") same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5)) and (fin or finfet or finmos\$4 or finmis\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:19
_	6	(((fill\$4 or refill\$4) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4") same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5)) and (fin or finfet or finmos\$4 or finmis\$4)) and (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 12:15
_	106805	(sidewall or wall or side) near10 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 12:17
-	121	<pre>((fin or finfet or finmos\$4 or finmis\$4) same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)) and (spacer or ((sidewall or wall or side) near10 gate))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 14:39
-	925	438/157.ccls. or 438/595.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 15:24
_	2	("6413802").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 15:25
_	2	("6252284").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/08/26 15:25